

# **BYC80MW-650PT2**

#### Hyperfast power diode

Rev.02 - 25 January 2024

**Product data sheet** 

#### 1. General description

Hyperfast power diode in a 2-lead TO247 plastic package.

### 2. Features and benefits

- · Fast switching and soft reverse recovery characteristics
- Low forward voltage drop
- Low leakage current
- Low reverse recovery current
- · Reduces switching losses in associated MOSFET or IGBT
- Package meets UL94V0 which guaranteed by Epoxy Mold Compound

### 3. Applications

- UPS
- EV Charger
- Welding Machine
- Air Conditioner

#### 4. Quick reference data

Table 1. Q	uick reference data						
Symbol	Parameter	Conditions	Notes	Values			Unit
Absolute	maximum rating						
$V_{\text{RRM}}$	repetitive peak reverse voltage				650		V
$I_{F(AV)}$	average forward current	δ = 0.5 ; square-wave pulse; T <sub>mb</sub> ≤ 91 °C; Fig. 1; Fig. 2; Fig. 3		80			A
I <sub>FRM</sub>	repetitive peak forward current	δ = 0.5 ; t <sub>p</sub> = 25 μs; T <sub>mb</sub> ≤ 91 °C; square-wave pulse		160			A
I <sub>FSM</sub> non-repetitive peak forward current		$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4		600		A	
		$t_{\rm p}$ = 8.3 ms; $T_{j(\text{init})}$ = 25 °C; sine-wave pulse		660			А
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static ch	aracteristics						
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 80 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>		-	1.95	2.50	V
		I <sub>F</sub> = 80 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>		-	1.46	1.90	V
Dynamic	characteristics				1	1	
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 50 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	44	-	ns

# **5. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	К	cathode		кКА
2	А	anode		001aaa020
mb	mb	mounting base; connected to cathod	Г. Д.	

# 6. Ordering information

Table 3. Ordering information								
Type number	Package name	Orderable part number	Packing method	Small packing quantity	• •	Package issue date		
BYC80MW-650PT2	TO247-2L	BYC80MW-650PT2Q	Tube	30	TO247L-2L (L) TO247P-2L (P)	10-Nov-2020 31-Mar-2023		

### 7. Marking

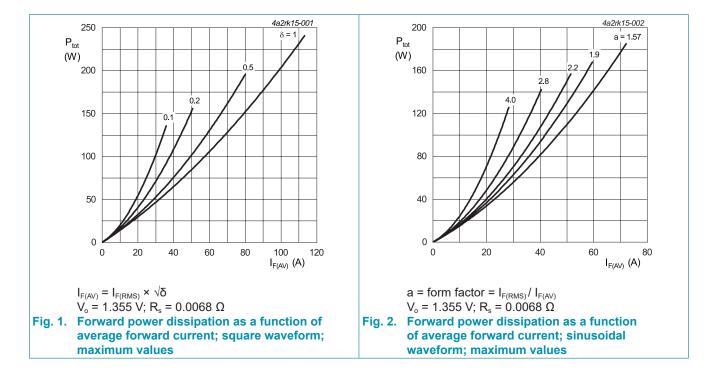
Table 4. Marking codes			
Type number	Marking codes		
	Assembly factory: L	Assembly factory: P	
BYC80MW-650PT2	BYC80MW 650PT2 PJLxxxx xx	BYC80MW 650PT2 PJPxxxx xx	

### 8. Limiting values

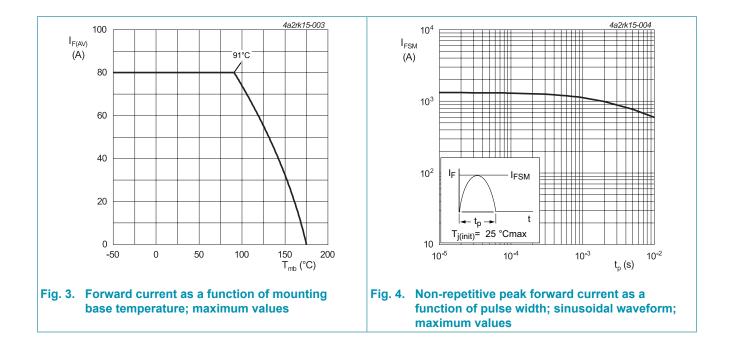
#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Values	Unit
$V_{RRM}$	repetitive peak reverse voltage			650	V
V <sub>RWM</sub>	crest working reverse voltage			650	V
V <sub>R</sub>	reverse voltage	DC		650	V
I <sub>F(AV)</sub>	average forward current	δ = 0.5 ; square-wave pulse; T <sub>mb</sub> ≤ 91 °C; Fig. 1; Fig. 2; Fig. 3		80	A
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5 ; t <sub>p</sub> = 25 µs; T <sub>mb</sub> ≤ 91 °C; square-wave pulse		160	A
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4		600	A
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse		660	А
T <sub>stg</sub>	storage temperature			-65 to 175	°C
T <sub>j</sub>	junction temperature			-65 to 175	°C

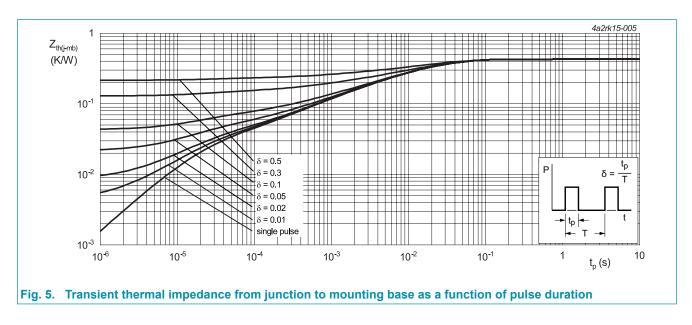


#### BYC80MW-650PT2 Hyperfast power diode



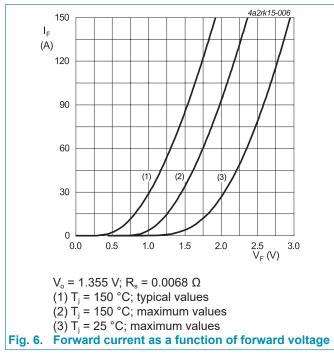
### 9. Thermal characteristics

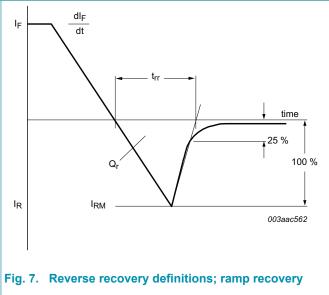
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	<u>Fig. 5</u>		-	-	0.43	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	in free air		-	40	-	K/W



### **10. Characteristics**

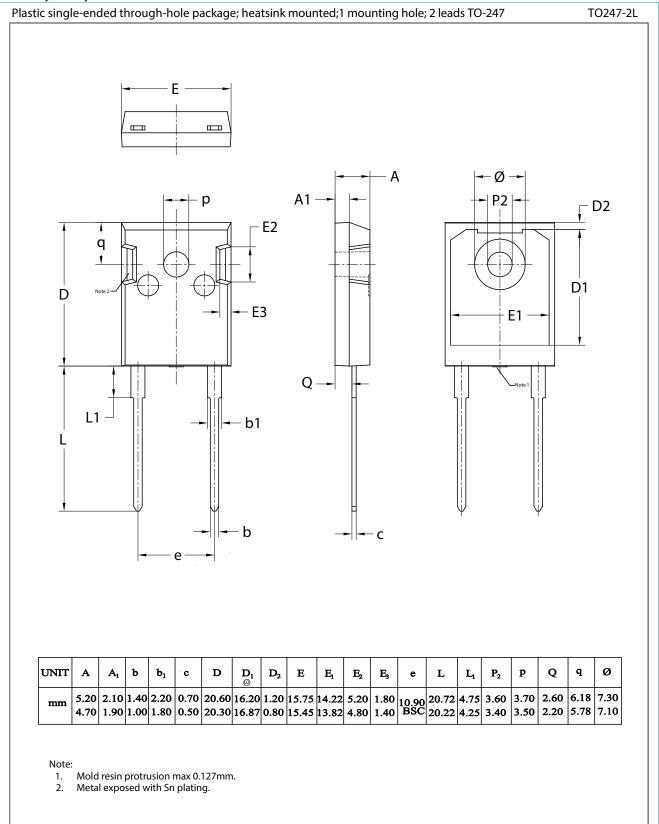
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
	aracteristics				- 71-		
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 80 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>		-	1.95	2.50	V
		I <sub>F</sub> = 80 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>		-	1.46	1.90	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 650 V; T <sub>j</sub> = 25 °C		-	0.8	30	μA
		V <sub>R</sub> = 650 V; T <sub>j</sub> = 150 °C		-	0.5	5	mA
Dynamic	characteristics				·		
Q <sub>r</sub>	reverse charge	$I_F = 50 \text{ A}; V_R = 400 \text{ V}; \text{ d}_F/\text{d}t = 500 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ Fig. 7}$		-	320	-	nC
		I <sub>F</sub> = 50 A; V <sub>R</sub> = 400 V; dI <sub>F</sub> /dt = 500 A/μs; T <sub>j</sub> = 125 °C; <u>Fig. 7</u>		-	1500	-	nC
t <sub>rr</sub>	reverse recovery time	I <sub>F</sub> = 1 A; V <sub>R</sub> = 30 V; dI <sub>F</sub> /dt = 50 A/μs; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>		-	44	-	ns
		$I_F = 50 \text{ A}; V_R = 400 \text{ V}; \text{ d}_F/\text{d}t = 500 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	60	-	ns
		I <sub>F</sub> = 50 A; V <sub>R</sub> = 400 V; dI <sub>F</sub> /dt = 500 A/μs; T <sub>j</sub> = 125 °C; <u>Fig. 7</u>		-	120	-	ns
I <sub>RM</sub>	peak reverse recovery current	$I_F = 50 \text{ A}; V_R = 400 \text{ V}; \text{ d}_F/\text{d}t = 500 \text{ A}/\mu\text{s};$ $T_j = 25 ^\circ\text{C}; \text{ Fig. 7}$		-	11	-	A
		$I_F = 50 \text{ A}; V_R = 400 \text{ V}; \text{ d}_F/\text{d}t = 500 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$		-	25	-	А
E <sub>as</sub>	non-repetitive avalanche energy	T <sub>j(init)</sub> = 25 °C		67.5	-	-	mJ



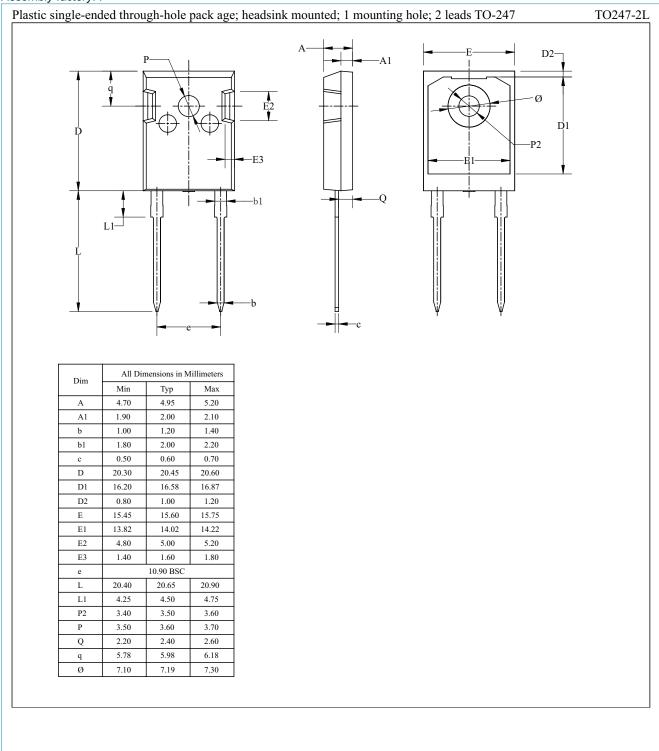


### **11. Package outline**

#### Assembly factory: L



#### Assembly factory: P



# BYC80MW-650PT2

#### Hyperfast power diode

### 12. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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